

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	5694	field near8 effect near8 transistor with (sensor or detector)	US- PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TD B
2	BRS	L2	3603	1 and (pore or hole or aperture or well)	US- PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TD B
3	BRS	L3	304	1 and (pore or hole or aperture or well) with insulat\$6 near6 (layer or coating or film or substrate)	US- PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
4	BRS	L4	148033	field near8 effect near8 transistor	US- PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TD B
5	BRS	L5	13883	4 and (pore or hole or aperture or well) with insulat\$6 near6 (layer or coating or film or substrate)	US- PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TD B
6	BRS	L6	199	4 and (pore or hole or aperture or well) with (pillar or column\$6 or cylindrical) with insulat\$6 near6 (layer or coating or film or substrate)	US- PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
7	BRS	L7	5	1 and (pore or hole or aperture or well) with (pillar or column\$6 or cylindrical) with insulat\$6 near6 (layer or coating or film or substrate)	US- PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TD B